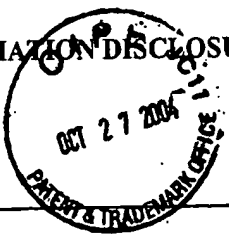




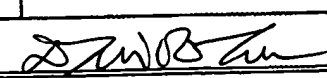
FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		ATTY DOCKET NO. 52139		SERIAL NO. 10/817,571	
		APPLICANT(S): Shenai-Khatkhate et al.			
		FILING DATE: 04/02/2004		ART UNIT: 2812	



UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPR

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRAN YES/NO

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)		
	AA	Masaki Okamoto; "Direct Synthesis of Organotrichlorogermanes by the Reaction of Elemental Germanium, Hydrogen Chloride and Alkene; Organometallics 2004, 23, pp. 595-599.
	AB	Bradley et al.; "Synthesis and characterisation of trialkylaluminium-dialkylamine adducts: X-ray diffraction and ¹ H NMR studies"; J. Chem. Soc., Dalton Trans. 1999, pp. 3553-3558.

Examiner: 	Date: 1/11/06
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FORM PTO-1449				ATTY DOCKET NO.		SERIAL NO.	
INFORMATION DISCLOSURE STATEMENT				52139		10/6/7571 Not Yet Assigned	
				APPLICANT(S): Shenai-Khatkhate			
				FILING DATE: Herewith		ART UNIT: Not Yet Assigned	
UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPR
<i>DN</i>	AA	2,444,270	06/29/1948	E. Rochow			—
	AB	3,446,824	05/27/1969	K. Moedritzer			—
	AC	4,506,815	03/26/1985	Melas et al.			—
	AD	3,470,220	09/30/1969	Moedritzer et al.			—
	AE	5,120,394	06/09/1992	Mukai			—
	AF	5,502,227	03/26/1996	Kanjolia et al.			—
	AG	5,755,885	05/26/1998	Mikoshiba et al.			—
	AH	6,099,903	08/08/2000	Kaloyeros et al.			—
	AI	6,214,729	04/10/2001	Uhlenbrock et al.			—
	AJ	6,238,734	05/29/2001	Senzaki et al.			—
	AK	6,306,217	10/23/2001	Uhlenbrock et al.			—
	AL	6,391,803	05/21/2002	Kim et al.			—
	AM	6,444,038	09/03/2002	Rangarajan et al.			—
	AN	6,444,041	09/03/2002	Vaartstra			—
	AO	6,444,818	09/03/2002	Uhlenbrock et al.			—
	AP	6,492,711	12/10/2002	Takagi et al.			—
	AQ	6,509,587	01/21/2003	Sugiyama et al.			—
	AR	6,514,886	02/04/2003	U'Ren			—
	AS	2003/0082300	05/01/2003	Todd et al.			—
<i>DN</i>	AT	2003/0111013	06/19/2003	Oosterlaken et al.			—
Examiner: <i>David R. D.</i>				Date: 1/11/06			

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		ATTY DOCKET NO. 52139		SERIAL NO. 10/81757/ Not Yet Assigned		
		APPLICANT(S): D. Shenai-Khatkhate				
		FILING DATE: Herewith		ART UNIT: Not Yet Assigned		
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS SUB CLASS	TRAN YES/NO
<i>BA</i>	BA	626,398	04/15/1946	United Kingdom	<i>X</i>	<i>X</i>
<i>BB</i>	BB	1 160 355 A2	12/05/2001	Europe	<i>X</i>	<i>X</i>
OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						
<i>CA</i>	CA	Dittmar et al., Cyclopentadienyl Germanes as Novel Precursors for the CVD of Thin Germanium Films, Chem. Vap. Deposition 2001, 7, No. 5, pp. 193-195.				
	CB	Harrison et al., "Predeposition Chemistry Underlying the Formation of Germanium Films by CVD of Tetravinylgermane", Chem. Mater. 1994, 6, pp. 1620-1626.				
	CC	Hoffman et al., "Plasma-enhanced chemical vapor deposition of silicon, germanium, and tin nitride thin films from metalorganic precursors", J. Vac. Sci. Technol. A 13(3), May/Jun 1995, pp. 820-825.				
	CD	O. Johnson, "The Germanes and Their Organo Derivatives", Chem. Rev. 1951, 48, 259, pp. 259-297.				
	CE	Kidd et al., "Germanium-73 Nuclear Magnetic Resonance Spectra of Germanium Tetrahalides", Journal of American Chemical Society, 95:1, January 10, 1973, pp. 88-90.				
	CF	H. Ohshima, "Organo-germanium adsorption on a silicon surface by excimer light irradiation", Applied Surface Science 107 (1996) pp. 85-89.				
	CG	Bottei et al., "Organogermanium Chemistry", Chem. Rev. (1951), 48, 259, pp. 403-442.				
	CH	Sulkes et al., "Molecular beam study of possible CVD intermediates from Group-14 organometallic precursors", Chemical Physics Letters 318 (2000) pp. 448-453.				
	CI	D. Smith, "Structural Properties of heteroepitaxial germanium-carbon alloys grown on Si (100); Philosophical Magazine A, 2001, Vol. 81, No. 6, pp. 1613-1624.				
<i>CJ</i>	CJ	Todd et al., "Influence on Precursor Chemistry on Synthesis of Silicon-Carbon Germanium Alloys", Mat. Res. Soc. Symp. Proc. Vol. 377, 1955, pp. 529-534.				
Examiner: <i>[Signature]</i>				Date: <i>1/11/06</i>		



FORM PTO-1449

INFORMATION DISCLOSURE STATEMENT

ATTY DOCKET NO.

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2812

UNITED STATES PATENT DOCUMENTS

EXAM. INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILE DATE
<i>M</i>	AA	3,935,040	01/27/1976	Mason			
	AB	3,985,590	10/12/1976	Mason			
	AC	4,720,561	01/19/1988	Bradley et al.			
	AD	4,812,586	03/14/1989	Mullin et al.			
	AE	5,316,958	05/31/1994	Meyerson			
	AF	5,489,550	02/06/1996	Moslehi			
	AG	2003/0230233 A1	12/18/2003	Fitzgerald et al.			
<i>W</i>	AH	2004/0259333 A1	12/23/2004	Tomasini et al.			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRAN YES/NO
<i>BZ</i>	BA	0 368 651 B1	09/07/1994	Europe	—	—	
<i>BZ</i>	BB	1 386 900	03/12/1975	United Kingdom	—	—	
<i>BZ</i>	BC	WO 2004/011473 A1	02/05/2004	International	—	—	

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

<i>W</i>	CA	Dillon et al.; "Comparison of Trichlorosilane and Trichlorogermane Decomposition on Silicon Surfaces Using FTIR Spectroscopy"; Mat. Res. Soc. Symp. Proc. Vol. 282; 1993; pp. 405-411.
	CB	Dillon et al.; "Adsorption and Decomposition of Diethylgermane on porous silicon surfaces"; Surface Science Letters 286 (1993); pp. L535-L541.
	CC	Todd et al.; "Chemical Synthesis of Metastable Germanium-Carbon Alloys Grown Heteroepitaxially on (100) Si; Chem. Mater. 1996, 8, pp. 2491-2498.
	CD	Coon et al.; "Germanium Deposition on Silicon: Surface Chemistry of (CH ₃ CH ₂) ₂ GeH ₂ and GeCl ₄ "; Mat. Res. Soc. Symp. Proc. Vol. 282; 1993; pp. 413-419.
	CE	Kouvetakis et al.; "Novel Chemical Routes to Silicon-Germanium-Carbon Materials"; Appl. Phys. Lett. 65 (23); 5 December 1994; pp. 2960-2962.
<i>W</i>	CF	Dillon et al.; "Adsorption and Decomposition of Trichlorosilane and Trichlorogermane on Porous Silicon and Si(100)2x1 Surfaces"; J. Vac. Sci. Technol. A 13(1); Jan/Feb 1995; pp. 1-10.

Examiner:

Dawson

Date:

1/11/06